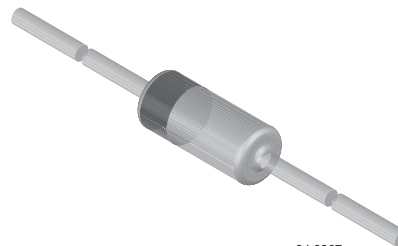


Small Signal Switching Diodes, High Voltage

Features

- Silicon Epitaxial Planar Diodes
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



94 9367

Applications

- General purposes

Mechanical Data

Case: DO35 Glass case

Weight: approx. 125 mg

Cathode Band Color: black

Packaging Codes/Options:

TR/10 k per 13" reel (52 mm tape), 50 k/box

TAP/10 k per Ammopack (52 mm tape), 50 k/box

Parts Table

Part	Type differentiation	Ordering code	Type Marking	Remarks
BAV17	$V_{RRM} = 25\text{ V}$	BAV17-TR or BAV17-TAP	BAV17	Tape and Reel/Ammopack
BAV18	$V_{RRM} = 60\text{ V}$	BAV18-TR or BAV18-TAP	BAV18	Tape and Reel/Ammopack
BAV19	$V_{RRM} = 120\text{ V}$	BAV19-TR or BAV19-TAP	BAV19	Tape and Reel/Ammopack
BAV20	$V_{RRM} = 200\text{ V}$	BAV20-TR or BAV20-TAP	BAV20	Tape and Reel/Ammopack
BAV21	$V_{RRM} = 250\text{ V}$	BAV21-TR or BAV21-TAP	BAV21	Tape and Reel/Ammopack

Absolute Maximum Ratings

$T_{amb} = 25\text{ °C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Peak reverse voltage		BAV17	V_{RRM}	25	V
		BAV18	V_{RRM}	60	V
		BAV19	V_{RRM}	120	V
		BAV20	V_{RRM}	200	V
		BAV21	V_{RRM}	250	V
Reverse voltage		BAV17	V_R	20	V
		BAV18	V_R	50	V
		BAV19	V_R	100	V
		BAV20	V_R	150	V
		BAV21	V_R	200	V
Forward continuous current			I_F	250	mA
Peak forward surge current	$t_p = 1\text{ s}, T_j = 25\text{ °C}$		I_{FSM}	1	A
Forward peak current	$f = 50\text{ Hz}$		I_{FRM}	625	mA
Power dissipation			P_{tot}	500	mW

Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction to ambient air	$l = 4\text{ mm}$, $T_L = \text{constant}$	R_{thJA}	300	K/W
Junction temperature		T_j	175	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 65 to + 175	$^{\circ}\text{C}$

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 100\text{ mA}$		V_F			1000	mV
Reverse current	$V_R = 20\text{ V}$	BAV17	I_R			100	nA
	$V_R = 50\text{ V}$	BAV18	I_R			100	nA
	$V_R = 100\text{ V}$	BAV19	I_R			100	nA
	$V_R = 150\text{ V}$	BAV20	I_R			100	nA
	$V_R = 200\text{ V}$	BAV21	I_R			100	nA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 20\text{ V}$	BAV17	I_R			15	μA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 50\text{ V}$	BAV18	I_R			15	μA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 100\text{ V}$	BAV19	I_R			15	μA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 150\text{ V}$	BAV20	I_R			15	μA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 200\text{ V}$	BAV21	I_R			15	μA
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$, $t_p/T = 0.01$, $t_p = 0.3\text{ ms}$	BAV17	$V_{(BR)}$	25			V
		BAV18	$V_{(BR)}$	60			V
		BAV19	$V_{(BR)}$	120			V
		BAV20	$V_{(BR)}$	200			V
		BAV21	$V_{(BR)}$	250			V
Diode capacitance	$V_R = 0$, $f = 1\text{ MHz}$		C_D		1.5		pF
Differential forward resistance	$I_F = 10\text{ mA}$		r_f		5		Ω
Reverse recovery time	$I_F = I_R = 30\text{ mA}$, $i_R = 3\text{ mA}$, $R_L = 100\text{ }\Omega$		t_{rr}			50	ns

Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

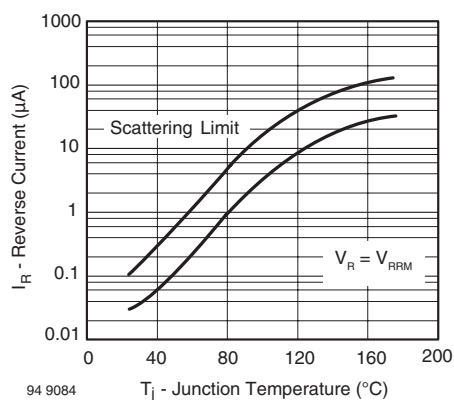


Figure 1. Reverse Current vs. Junction Temperature

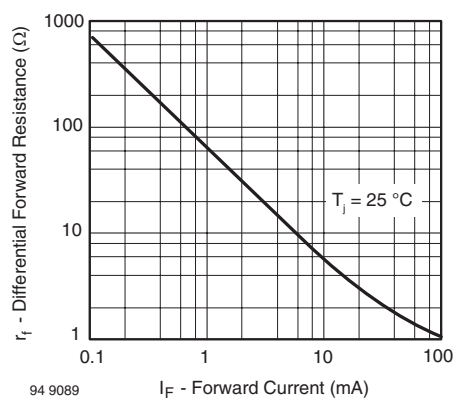


Figure 3. Differential Forward Resistance vs. Forward Current

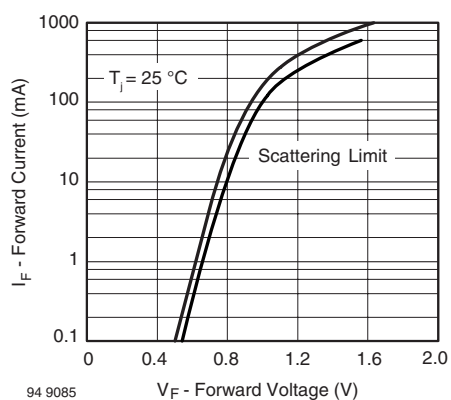


Figure 2. Forward Current vs. Forward Voltage

Package Dimensions in millimeters (inches): DO35

